

ABSTRACT OF DISCLOSURE

In a thin film transistor having a semiconductor film provided above a substrate, a gate insulating film covering the semiconductor film, a gate electrode formed on the gate insulating film, and an interlayer insulating film covering the gate electrode, the gate electrode has a tapered shape wherein the width becomes wider from the side of the interlayer insulating film towards the gate insulating film. With this structure, the characteristics are stabilized. The electrode having a tapered shape can be formed through a first etching step wherein etching is applied to an electrode material layer to a degree where at least a portion of the electrode material layer remains and a second etching step wherein etching is applied to the electrode material layer while the mask is being ashed.